

捷多邦,专业PCB打样工厂,24小时加急出货

Ordering number:EN3243

NPN Triple Diffused Planar Silicon Transistor

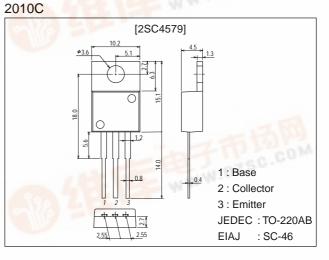


Features

- · High breakdown voltage.
- · Small Cob.
- · Wide ASO.
- · High reliability (Adoption of HVP process).

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|------------------|-------------------------------------------|-------------|------|
| Collector-to-Base Voltage | V _{CBO} | | 2000 | V |
| Collector-to-Emitter Voltage | V _{CEO} | | 900 | V |
| Emitter-to-Base Voltage | V _{EBO} | | 5 | V |
| Collector Current | IC | | 20 | mA |
| Collector Current (Pulse) | ICP | 1 4 A S S S S S S S S S S S S S S S S S S | 60 | mA |
| Collector Dissipation | PC | | 1.75 | W |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

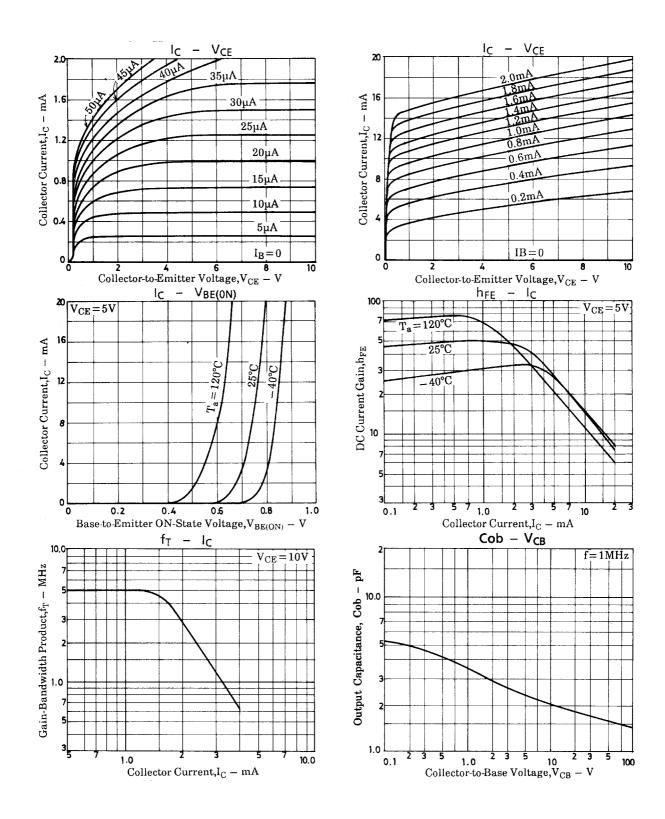
Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|-----------------------------------------|----------------------|--------------------------------------------|---------|-------|------|------|
| | | Conditions | | typ | max | Unit |
| Collector Cutoff Current | ICBO | V _{CB} =900V, I _E =0 | | | 1 | μA |
| Emitter Cutoff Current | IEBO | $V_{EB}=4V, I_{C}=0$ | | | - 1 | μA |
| DC Current Gain | hFE | V _{CE} =5V, I _C =1mA | 20 | 50 | 120 | 100 |
| Gain-Bandwidth Product | fT | V _{CE} =10V, I _C =1mA | 101- | 6 | 100 | MHz |
| Output Capacitance | Cob | V _{CB} =100V, f=1MHz | 10-1 | 1.6 | 1200 | pF |
| Collector-to-Emitter Saturation Voltage | VCE(sat) | I _C =2mA, I _B =0.4mA | 11.14 | 12000 | 5 | V |
| Base-to-Emitter Saturation Voltage | V _{BE(sat)} | I _C =2mA, I _B =0.4mA | | | 2 | V |

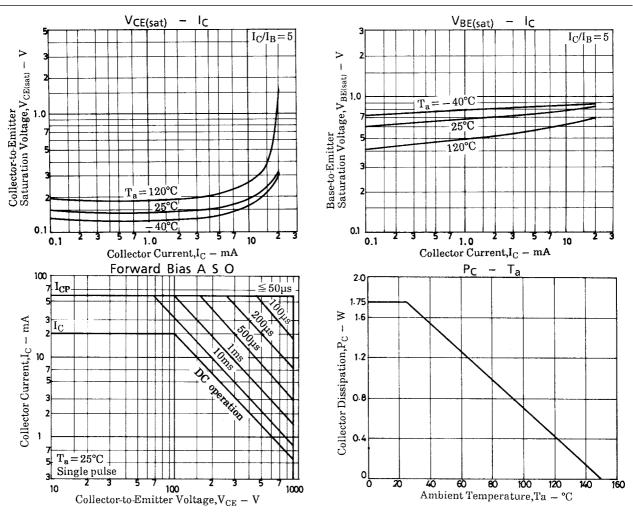
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| Parameter | Symbol | Conditions | Ratings | | | Unit |
|----------------------------------------|-----------------------|-----------------------------------------|---------|-----|-----|------|
| | | | min | typ | max | Onit |
| Collector-to-Base Breakdown Voltage | V _(BR) CBO | I _C =1mA, I _E =0 | 2000 | | | V |
| Collector-to-Emitter Breakdown Voltage | V _(BR) CEO | I _C =1mA, R _{BE} =∞ | 900 | | | V |
| Emitter-to-Base Breakdown Voltage | V(BR)EBO | I _E =1mA, I _C =0 | 5 | | | V |



2SC4579



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